

Amendments to the Claims:

None

Listing of Claims:

Claims 1-15 (canceled)

Claim 16 (original): A transistor formed using a method, comprising:

implanting at least a halogen species within an at least partially formed semiconductor device to form at least one amorphous region;

doping at least a portion of the at least one amorphous region to form at least one junction within the at least partially formed semiconductor device; and

activating the doped portion of the at least one amorphous region of the at least partially formed semiconductor device by solid phase epitaxial re-growth.

Claim 17 (original): The transistor of Claim 16, wherein the at least a halogen species comprises fluorine.

Claim 18 (original): The transistor of Claim 16, wherein the at least one junction is doped with at least a boron dopant.

Claim 19 (original): The transistor of Claim 16, wherein an amorphous depth (X_a) associated with the at least one amorphous region is greater than or equal to a junction depth (X_j) associated with the at least one junction.

Claim 20 (original): The transistor of Claim 16, wherein an amorphous depth (X_a) associated with the at least one amorphous region is less than or equal to a junction depth (X_j) associated with the at least one junction.

Amendments to the Drawings:

None